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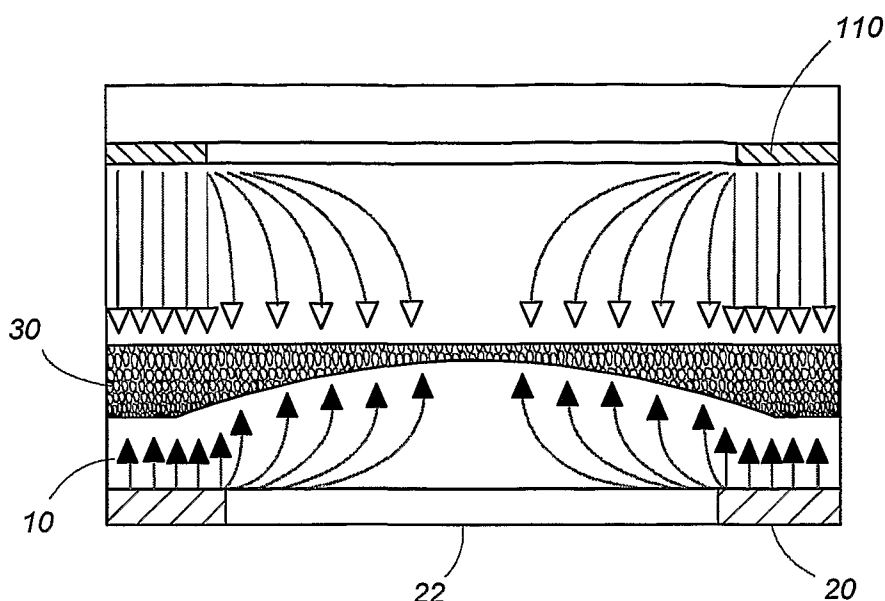
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(54) Title: PROCESS OF MAKING A SEMICONDUCTOR OPTICAL LENS AND A SEMICONDUCTOR OPTICAL LENS FABRICATED THEREBY



(57) Abstract: A semiconductor substrate with anode pattern is anodized to be shaped into an optical lens. The anodization utilizes an electrolytic solution which etches out oxidized portion as soon as it is formed as a result of the anodization, to thereby develop a porous layer in a pattern in match with the anode pattern. After being removed of the porous layer, the substrate is treated to smooth out minute projections remaining in the top surface of the substrate, thereby obtaining the lens of good transmissivity.

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